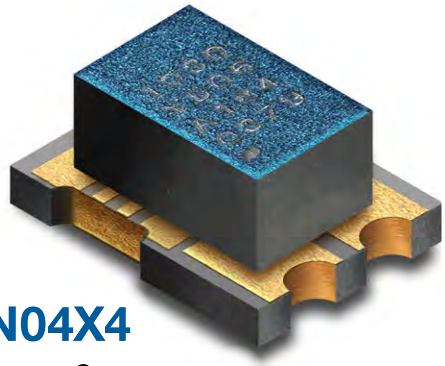
CDA20N04X4 Datasheet

Features

- Low $R_{DS(on)}$
- Ultra-low Q_G For High Efficiency
- Logic Level
- Light Weight
- New Compact Die Adaptor Assembly
- Source Sense Pin
- Total Dose
  - Rated to 300 krad
- Single Event
  - SEE immunity for LET of 83.7 MeV/mg/cm^2 with V_{DS} up to 100% of rated Breakdown
- Low Dose Rate at 100 mRad/sec
  - Maintains Pre-Rad specification
- Neutron
  - Maintains Pre-Rad specification for up to 1 x 10^{13} Neutrons/cm^2

Application

- Commercial Satellite EPS & Avionics
- Deep Space Probes
- High Speed Rad Hard DC-DC Conversion
- Rad Hard Motor Controllers



CDA20N04X4

Rad Hard e-GaN® 200 V, 4 A, 100 mΩ Die Adaptor Product (CDA4)

Description

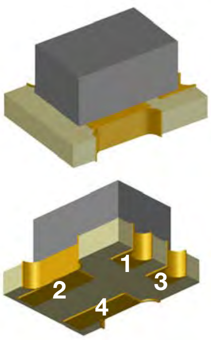
EPC Space CDA series of eGaN® power switching HEMTs have been specifically designed for critical applications in the high reliability or commercial satellite space environments. These devices have exceptionally high electron mobility and a low temperature coefficient resulting in very low $R_{DS(on)}$ values. The lateral structure of the die provides for very low gate charge (Q_G) and extremely fast switching times. These features enable faster power supply switching frequencies resulting in higher power densities, higher efficiencies and more compact circuitry.

Thermal Characteristics

Symbol	Parameter-Conditions	Value	Units
$R_{\theta JA}$	Thermal Resistance Junction to Ambient (Note 3)	90	°C/W
$R_{\theta JC}$	Thermal Resistance Junction to Case	5.12	

I/O Pin Assignment *(Bottom View)*

Pin	Symbol	Description
1	G	Gate
2	D	Drain
3	SS	Source Sense
4	S	Source



Absolute Maximum Rating *(T_C = 25°C unless otherwise noted)*

Symbol	Parameter-Conditions	Value	Units
V_{DS}	Drain to Source Voltage (Note 1)	200	V
I_D	Continuous Drain Current I_D @ V_{GS} = 5 V, T_C = 25°C, $R_{\theta JA}$ < 26 °C/W	4	A
I_{DM}	Single-Pulse Drain Current $t_{pulse} \leq$ 270 µs	16	
V_{GS}	Gate to Source Voltage (Note 2)	+6 / -4	V
T_J , T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C
T_{sol}	Package Mounting Surface Temperature	260	
ESD	ESD Class	1A	

Electrical Characteristics *(T_C = 25°C unless otherwise noted. Typical (TYP) values are for reference only.)*

Parameter	Symbol	Test Conditions		MIN	TYP	MAX	Units
Maximum Drain to Source Voltage	V_{DSMAX}	V_G = 0 V		-	-	200	V
Drain to Source Leakage	I_{DSS}	V_{DS} = 200 V, V_{GS} = 0 V	T_C = 25°C	-	26	50	µA
			T_C = 125°C	-		100	
Gate to Source Forward Leakage	I_{GSS}	V_{GS} = 5 V	T_C = 25°C	-	0.5	1.0	mA
Gate to Source Reverse Leakage	I_{GSS}	V_{GS} = -4 V	T_C = 25°C		-5	-50	µA
Gate to Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS} , I_D = 1 mA	T_C = 25°C	0.8	1.2	2.8	V
Gate to Source Threshold Voltage Temperature Coefficient	$\Delta V_{GS(th)}/\Delta T$	V_{DS} = V_{GS} , I_D = 1 mA	-55°C < T_A < 150°C	-	|2.4|	-	mV/°C
Drain to Source Resistance (Note 4)	$R_{DS(on)}$	I_D = 4 A, V_{GS} = 5 V	T_C = 25°C	-	65	100	mΩ
Source to Drain Forward Voltage (Note 5)	V_{SD}	I_S = 0.5 A, V_G = 0 V	T_C = 25°C		1.75		V

Dynamic Characteristics *(T_C = 25°C unless otherwise noted. Typical (TYP) values are for reference only.)*

Parameter	Symbol	Test Conditions	MIN	TYP	MAX	Units
Input Capacitance	C_{ISS}	f = 1 MHz, V_{DS} = 100 V, V_{GS} = 0 V (Note 6)		106	150	pF
Output Capacitance	C_{OSS}			72	90	
Reverse Transfer Capacitance	C_{RSS}			2	6	
Gate Resistance	R_G	f = 1 MHz, V_{DS} = V_{GS} = 0 V		0.6		Ω
Total Gate Charge (Note 7)	Q_G	I_D = 4 A, V_{GS} = 5 V, V_{DS} = 100 V		1.6	3	nC
Gate to Drain Charge (Note 7)	Q_{GD}			0.2	1	
Gate to Source Charge (Note 7)	Q_{GS}			0.5	1.8	
Output Charge (Note 8)	Q_{OSS}	V_{GS} = 0 V, V_{DS} = 100 V		13		
Source to Drain Recovery Charge	Q_{RR}	I_D = 4 A, V_{DS} = 100 V		<1		

Radiation Characteristics

EPC Space eGaN® HEMTs are tested according to MIL-STD-750 Method 1019 for total ionizing dose validation. Every manufacturing lot is tested for total ionizing dose of Gamma radiation with an in-situ bias for (i) V_{GS} = 5 V, (ii) V_{DS} = V_{GS} = 0 V and (iii) V_{DS} = 80% B_{VDSS}.

Electrical Characteristics up to 300 krads *(T_C = 25°C unless otherwise noted. Typical (TYP) values are for reference only.)*

Parameter	Symbol	Test Conditions	MIN	TYP	MAX	Units
Maximum Drain to Source Voltage	V_{DSMAX}	V_{GS} = 0 V	-	-	200	V
Gate to Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS} , I_D = 1 mA	0.8	1.0	2.8	V
Drain to Source Leakage	I_{DSS}	V_{DS} = 200 V, V_{GS} = 0 V	-	26	50	µA
Gate to Source Forward Leakage	I_{GSS}	V_{GS} = 5 V	-	0.5	1.0	mA
Gate to Source Reverse Leakage	I_{GSS}	V_{GS} = -4 V	-	-5	-50	µA
Drain to Source Resistance (Note 4)	$R_{DS(on)}$	I_D = 4 A, V_{GS} = 5 V	-	65	100	mΩ

Typical Single Event Effect Safe Operating Area

Note : All Single Event Effect testing is performed on the K-500 Cyclotron at Texas A&M University

Test	Environment				V_{DS} Voltage (V)	
See SOA	Ion	LET MeV/mg/cm^2	Range µm	Energy MeV	V_{GS} = 0 V	V_{GS} = -4V
	Xe	50	131	1653	200	200
	Au	83.7	130	2482	175	175

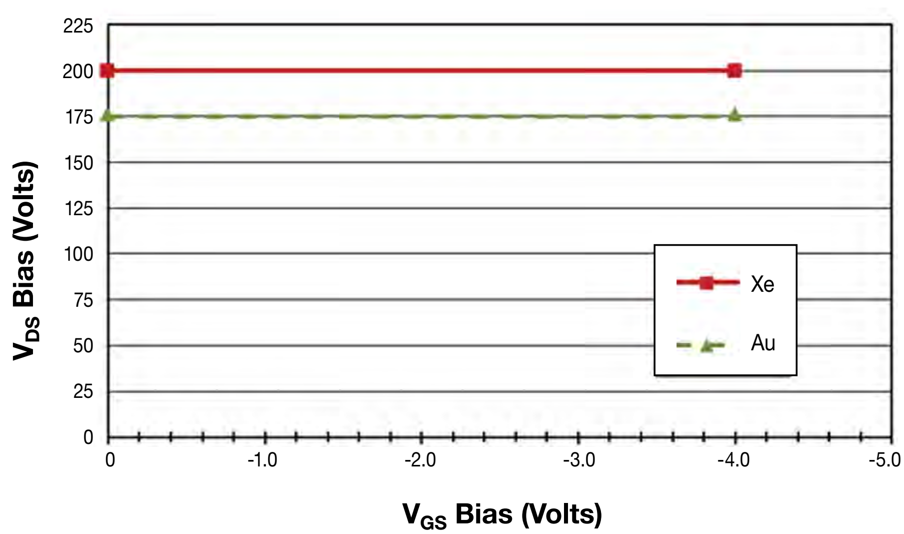


Figure 1. Typical Single Event Effect Safe Operating Area

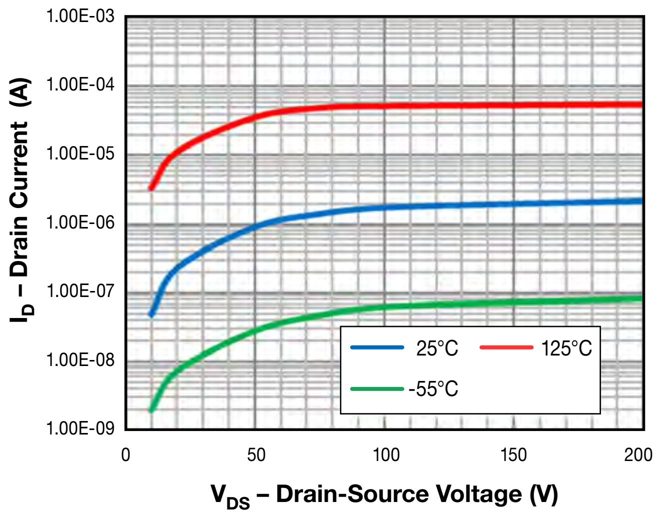


Figure 2. Typical Drain-Source Leakage Current vs. Ambient Temperature

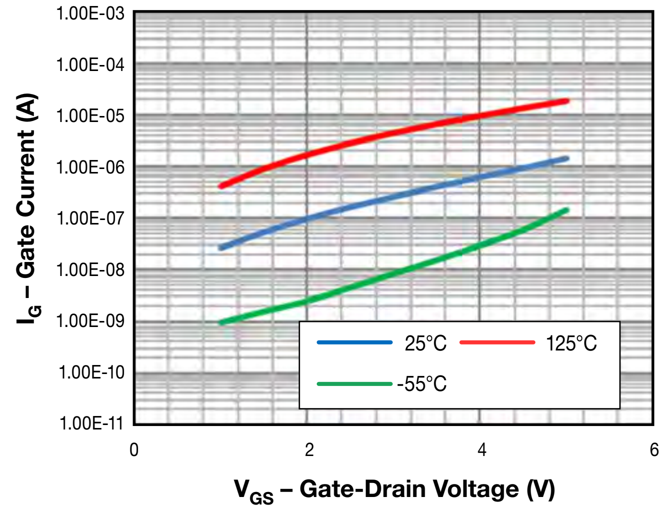


Figure 3. Gate-Source Leakage Current vs. Ambient Temperature

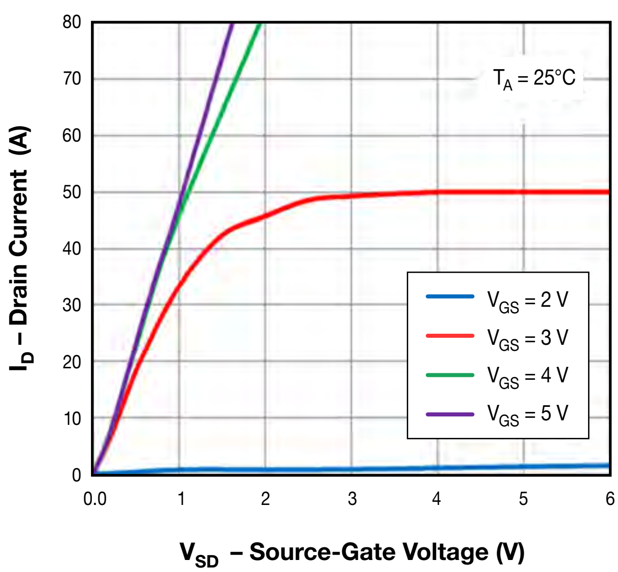


Figure 4. Typical Gate-Drain Transfer Characteristic

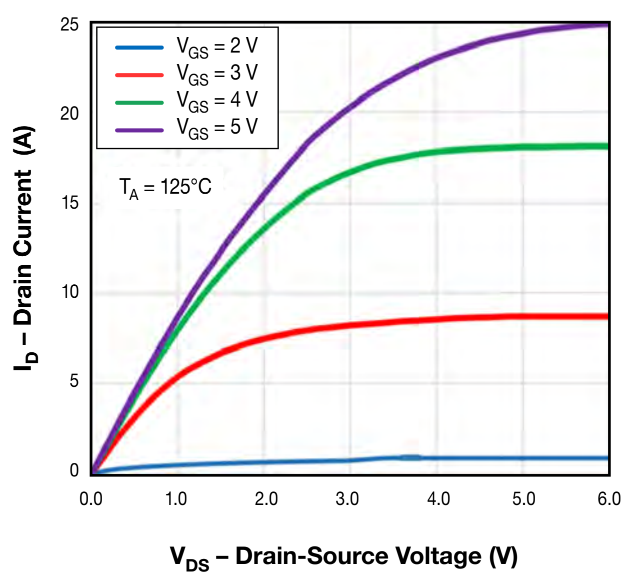


Figure 5. Typical Output Characteristics

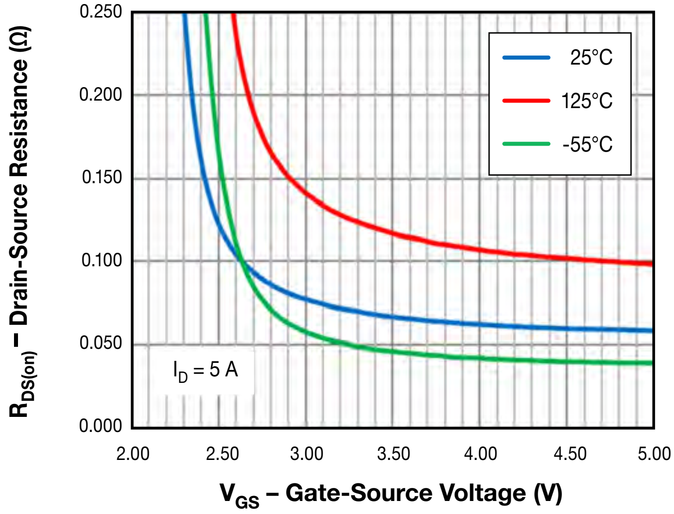


Figure 6. Typical Drain-Source ON Resistance vs. Gate-Source Voltage vs. Ambient Temperature

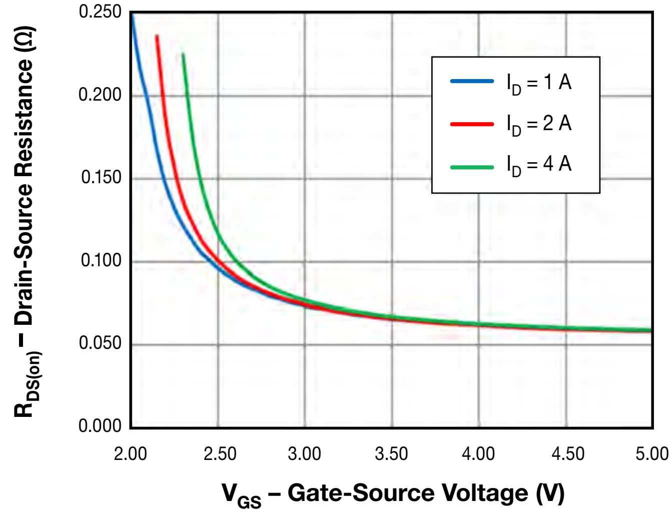


Figure 7. Typical Drain-Source ON Resistance vs. Gate-Source Voltage vs. Drain Current

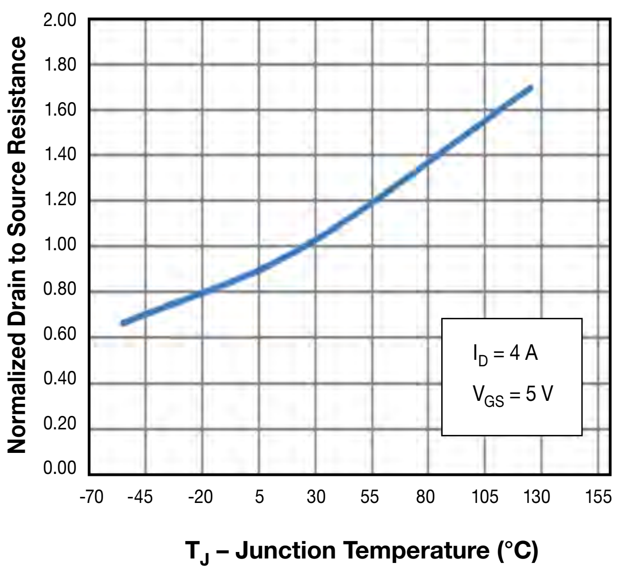


Figure 8. Typical Source-Drain Voltage vs. Temperature

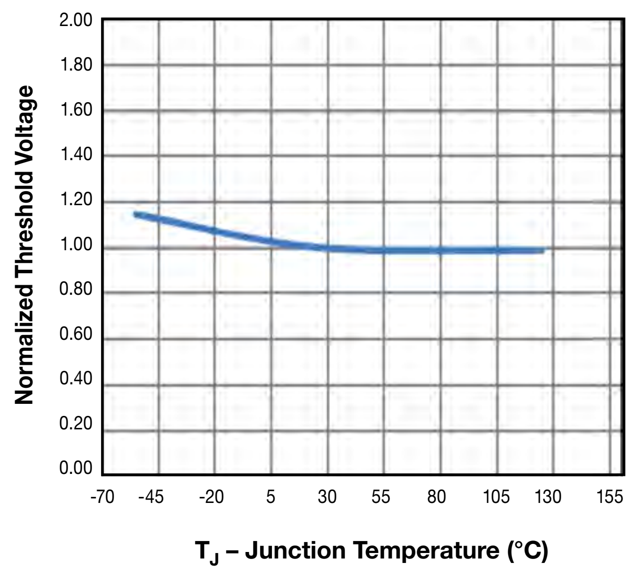


Figure 9. Normalized Drain-Source ON Resistance vs. Ambient Temperature

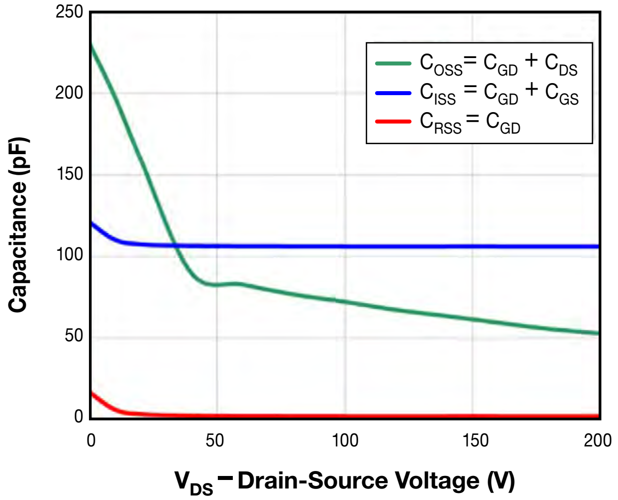


Figure 10. Typical Inter-Electrode Capacitance vs. Drain-Source Voltage

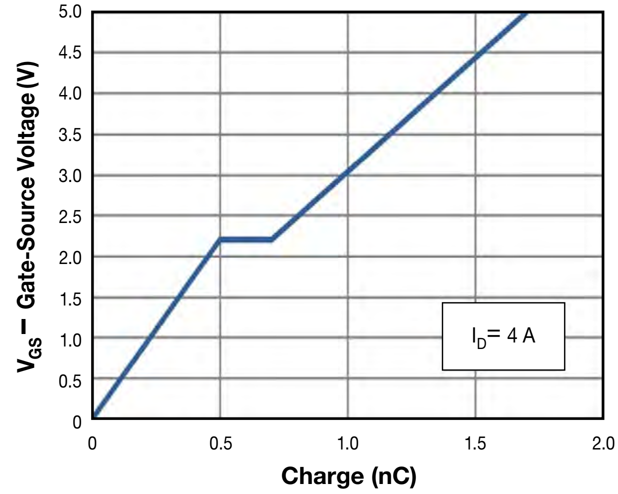


Figure 11. Typical Gate Charge vs. Drain Current

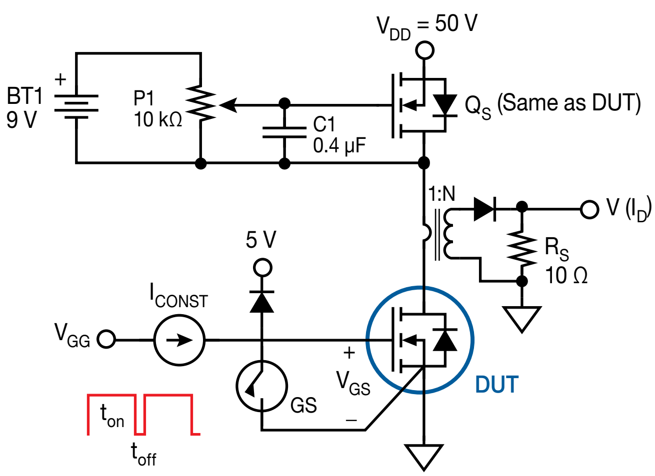


Figure 12. Charge Test Circuit

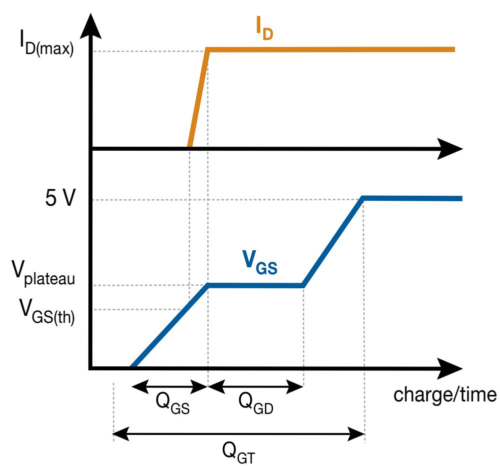
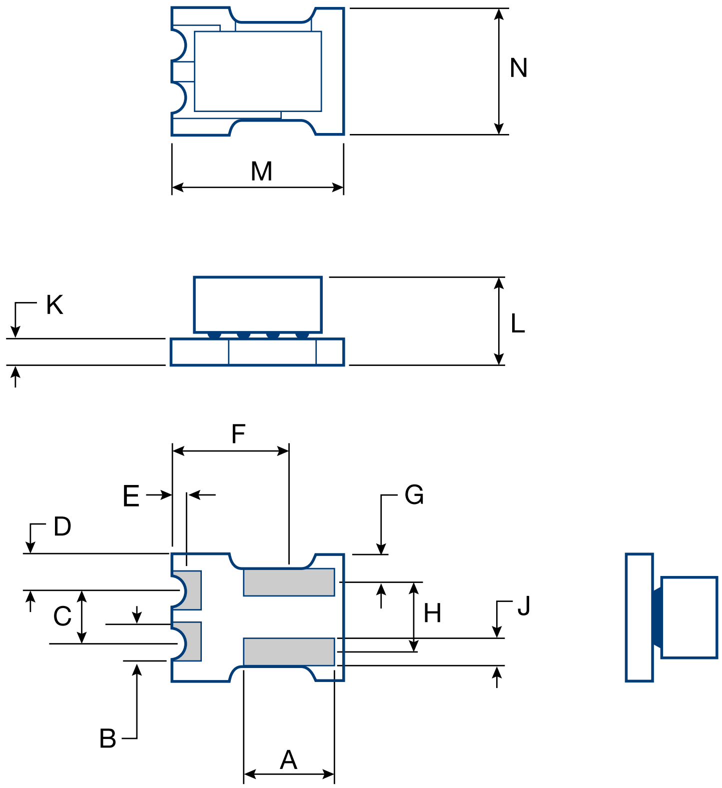


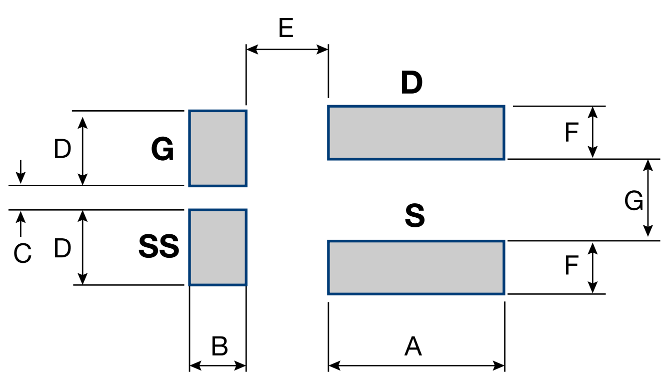
Figure 13. Typical Gate Charge Test Waveform

Package Outline and Dimensions



Symbol	Inches	Millimeters	Note
A	0.047	1.193	
B	0.020	0.508	
C	0.028	0.711	
D	0.016	0.406	
E	0.008	0.203	
F	0.063	1.600	
G	0.016	0.406	
H	0.036	0.914	
J	0.015	0.381	
K	0.015	0.381	
L	0.047	1.194	Ref.only
M	0.091	2.311	
N	0.060	1.524	

CDA4 Footprint for Printed Circuit Board Design



Symbol	Inches	Millimeters	Note
A	0.051	1.295	
B	0.019	0.483	
C	0.008	0.203	
D	0.020	0.508	
E	0.032	0.813	
F	0.020	0.508	
G	0.024	0.610	
H	0.037	0.940	

Notes

Note 1. NEVER exceed the absolute maximum V_{DS} of the device otherwise permanent damage/destruction may result.

Note 2. NEVER exceed the absolute maximum V_{GS} of the device otherwise permanent damage/destruction may result. We recommend use at no greater than +5 V as the HEMT is fully conducting at this point.

Note 3. $R_{\theta JA}$ measured with CDA1 package mounted to double-sided PCB, 0.063" thickness with 1.0 square inches of copper area on the top (mounting side) and a flood etch (3 square inches) on the bottom side.

Note 4. Measured using four wire (Kelvin) sensing and pulse measurement techniques. Measurement pulse width is 80 µs and duty cycle is 1%, maximum.

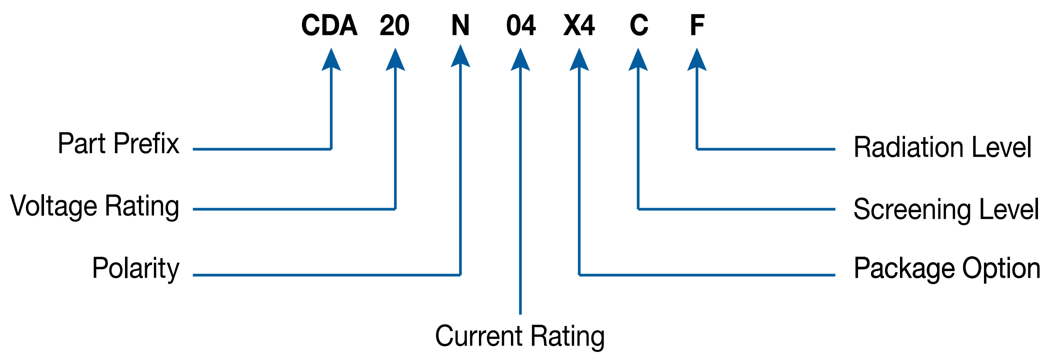
Note 5. With pulse measurement width 100–380 µs.

Note 6. $C_{ISS} = C_{GS} + C_{GD}$ with C_{DS} shorted. $C_{OSS} = C_{DS} + C_{GD}$. $C_{RSS} = C_{GD}$.

Note 7. The gate charge parameters are measured using the circuit shown in Figure 14. Qs and associated components BT1, P1 and C1 form a high speed current source that serves as the test load for the DUT. A constant gate current (I_{const}) of 1.5-3 mA is provided to the Gate of the DUT during the time that the ground switch (G_S) is OFF (t_{off}). The DUT is switched ON and OFF using ground-sensed switch GS. The gate current is adjusted to yield the desired charge per unit time (I_{const} · time per division) on the measuring oscilloscope. The GS pulse drive ON time (t_{on})is adjusted for the desired observability of the gate-source voltage (V_{GS}) waveform. The maximum duty cycle of the ground switch (t_{off} /t_{on}) should be set to 1% maximum. Please note that all gate-related signals are referenced to the "Source Sense" pin on the package. At all times during the measurement, the maximum gate-source voltage is clamped to 5 V_{DC}.

Note 8. Guaranteed by design/device construction. Not tested.

EPC Space Part Number Information



Ordering Information Availability

Screening Options	Rad Assurance Options
1 character	1 character
C = Developmental Unit V = Lite Screened	R = 100 krad, LET = 64 F = 300 krad, LET = 64 G = 500 krad, LET = 64 H = 1000 krad, LET = 64 Z = 1000 krad, LET = 84

Part Number	Screening Level	Shipping
CDA20N04X4*C	Engineering Samples	Waffle Trays
CDA20N04X4*S	Space Level	

[1] Screening and qualification consistent to an equivalent MIL-PRF-19500 specification (KC).

C version CDA units are intended for engineering development purposes only and NOT supplied with radiation performance guarantees nor supplemental data packages

Data Package Order Detail
Consistent to MIL-PRF-19500 general specification

SPACE Screen

1. CDA20N04X4*S – OPTIONAL DATA PACKAGE

A. Certificate of Compliance

B. Serialization Records

C. Preconditioning – Attributes Data Sheet (Lot Sample)

– HTGB - Hi Temp Gate Stress Post Reverse Bias Data

– HTRB - Hi Temp Drain Stress Post Reverse Bias Data

D. Group A – Attributes Data Sheet

E. Group B – Selected Mechanical Stress Test

F. Group D – Attributes Data Sheet

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Datasheet Revision	Product Status
REV P#	Proposal/development
REV Q#	Characterization and Qualification
M-701-005-D	Production Released

Information subject to change without notice.
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